

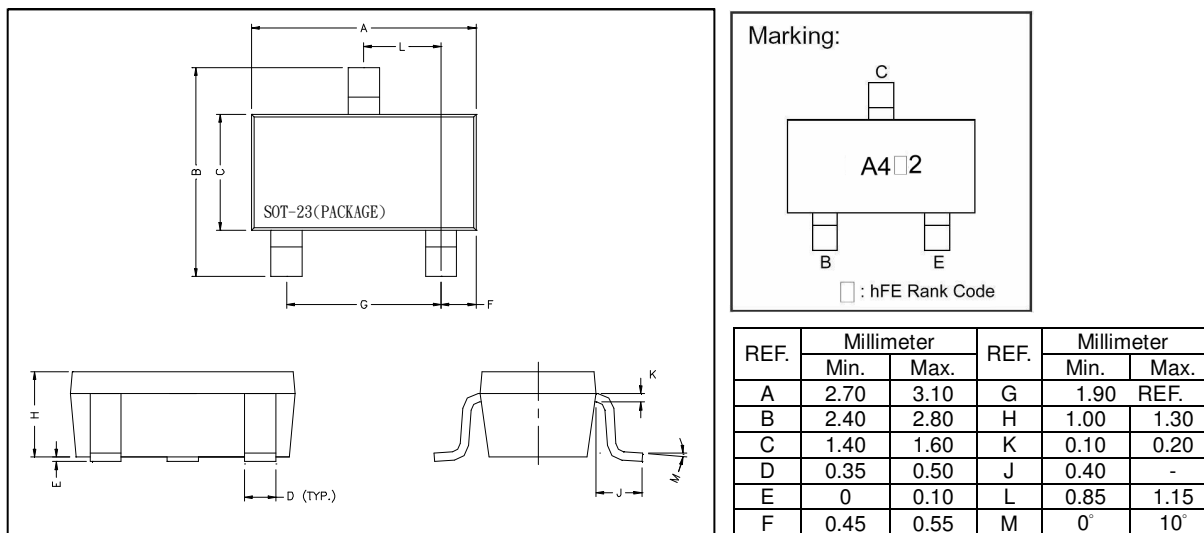
GMBT9012

PNP EPITAXIAL TRANSISTOR

Description

The GMBT9012 is designed for use in 1W output amplifier of portable radios in class B push-pull operation.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-40	V
Collector to Emitter Voltage	VCEO	-20	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	I _C	-500	mA
Total Power Dissipation	PD	225	mW

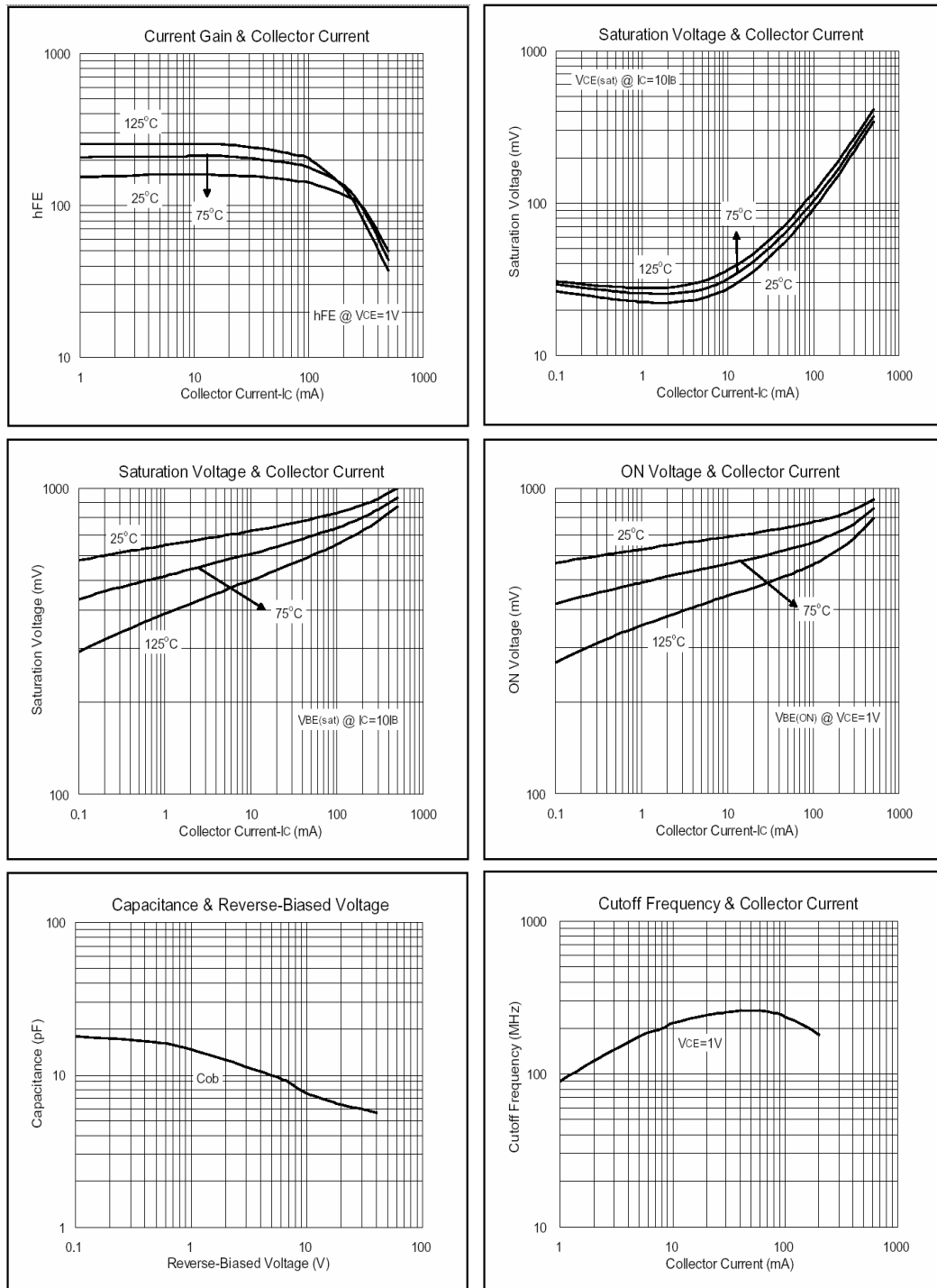
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	I _C =-100uA, I _E =0
BVCEO	-20	-	-	V	I _C =-1mA, I _B =0
BVEBO	-5	-	-	V	I _E =-100uA, I _C =0
ICBO	-	-	-100	nA	V _{CE} =-25V, I _E =0
IEBO	-	-	-100	nA	V _{EB} =-3V, I _C =0
VCE(sat)	-	-	-0.6	V	I _C =-500mA, I _B =-50mA
VBE(sat)	-	-	-1.2	V	I _C =-500mA, I _B =-50mA
VBE(on)	-	-	-0.9	V	V _{CE} =-1V, I _C =-10mA
hFE1	112	180-	300		V _{CE} =-1V, I _C =-50mA
hFE2	40	-	-		V _{CE} =-1V, I _C =-500mA
f _T	100	-	-	MHz	V _{CE} =-1V, I _C =-10mA, f=100MHz
Cob	-	-	8	pF	V _{CB} =-10V, f=1MHz

Classification Of HFE1

Rank	G	H	L
hFE	112 - 166	144 - 202	176 - 300

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165